

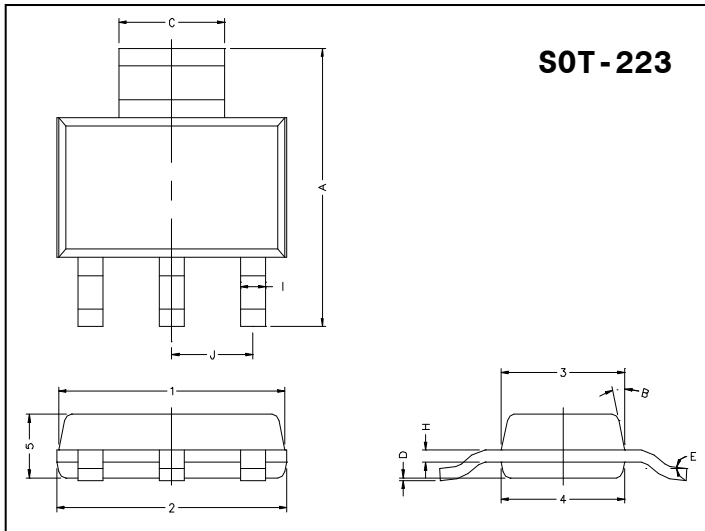
## GL5401

### PNP EPITAXIAL PLANAR TRANSISTOR

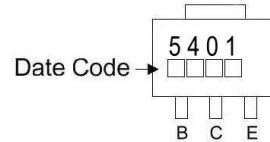
#### Description

The GL5401 is designer for general purpose applications requiring high breakdown voltages.

#### Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13° TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T <sub>j</sub>	+150	°C
Storage Temperature	T <sub>stg</sub>	-55 ~ +150	°C
Collector to Base Voltage	V <sub>CB0</sub>	-160	V
Collector to Emitter Voltage	V <sub>CEO</sub>	-150	V
Emitter to Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current	I <sub>C</sub>	-600	mA
Total Power Dissipation	P <sub>D</sub>	1.5	W

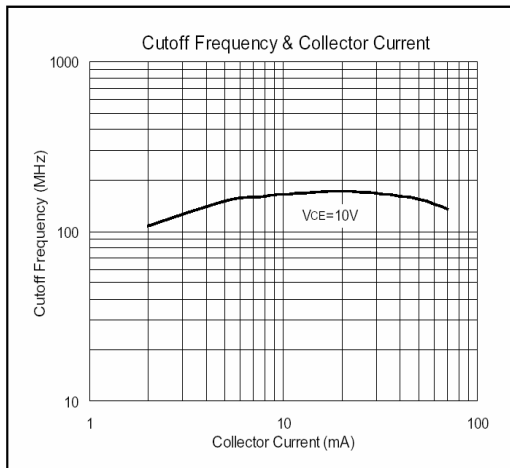
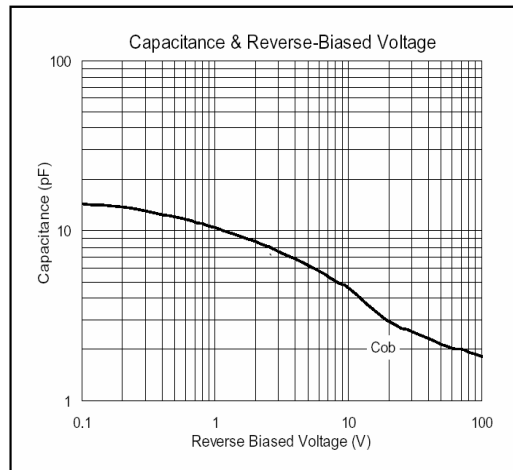
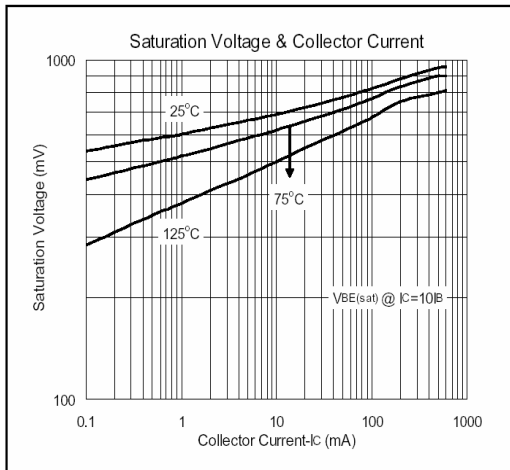
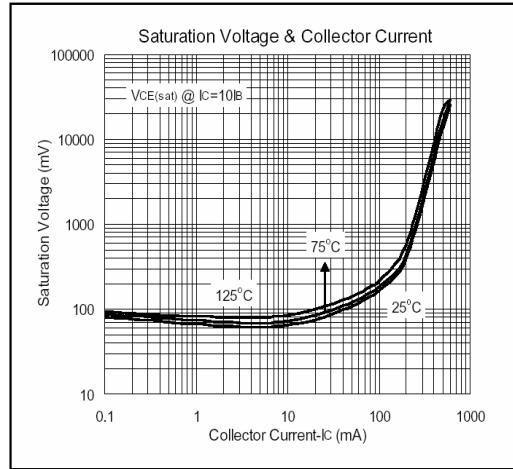
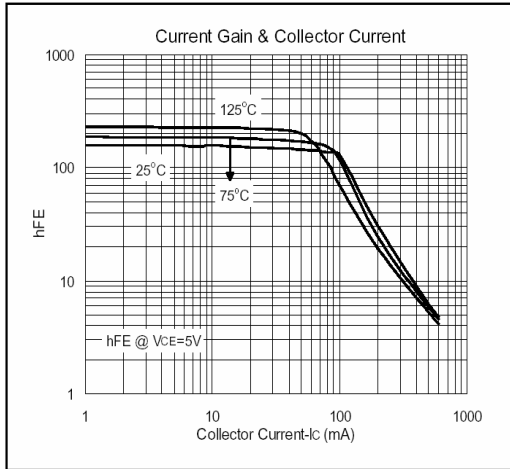
#### Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V <sub>CB0</sub>	-160	-	-	V	I <sub>C</sub> =-100uA, I <sub>E</sub> =0
V <sub>CEO</sub>	-150	-	-	V	I <sub>C</sub> =-1mA, I <sub>B</sub> =0
V <sub>EBO</sub>	-5	-	-	V	I <sub>E</sub> =-10uA, I <sub>C</sub> =0
I <sub>CB0</sub>	-	-	-50	nA	V <sub>CB</sub> =-120V, I <sub>E</sub> =0
I <sub>EBO</sub>	-	-	-50	nA	V <sub>EB</sub> =-3V, I <sub>C</sub> =0
V <sub>CE(sat)1</sub>	-	-	-200	mV	I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA
V <sub>CE(sat)2</sub>	-	-	-500	mV	I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA
V <sub>BE(sat)1</sub>	-	-	-1	V	I <sub>C</sub> =-10mA, I <sub>B</sub> =-1mA
V <sub>BE(sat)2</sub>	-	-	-1	V	I <sub>C</sub> =-50mA, I <sub>B</sub> =-5mA
h <sub>FE1</sub>	50	-	-		V <sub>CE</sub> =-5V, I <sub>C</sub> =-1mA
h <sub>FE2</sub>	80	160	400		V <sub>CE</sub> =-5V, I <sub>C</sub> =-10mA
h <sub>FE3</sub>	50	-	-		V <sub>CE</sub> =-5V, I <sub>C</sub> =-50mA
f <sub>T</sub>	100	-	300	MHz	V <sub>CE</sub> =-10V, I <sub>C</sub> =-10mA, f=100MHz
C <sub>ob</sub>	-	-	6	pF	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz

#### Classification Of hFE

Rank	A	N	C
Range	80 - 200	100 - 240	160 - 400

## Characteristics Curve



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